

IN THE SPECIFICATION

Please insert the following section after the title of the application as follows:

**--CROSS-REFERENCE TO RELATED APPLICATION**

This Application is related to commonly owned co-pending Provisional Application Serial Number 60/168,212, filed November 30, 1999 and claims the benefit of its earlier filing date under 35 U.S.C. § 119(e).--

Please replace the paragraph beginning at line 2 of page 11 with the following rewritten paragraph:

--Figure 5B depicts the semiconductor device 200 after step 110 or 122, removal of the ARC layer 232. A second layer of components can be fabricated on the ILD 230. Because the ARC layer 232 has been removed, the memory cells 210 and 220 can be erased using UV light. Moreover, the CMP step was omitted in lieu of, for example, a plasma etch. Thus, the unanticipated charge gain or unanticipated charge loss are reduced beyond that achieved using conventional CMP for removing the ARC layer 232.--

REMARKS

Claims 1-7 are pending in the Application. Claims 1 and 6 are rejected under 35 U.S.C. § 102(e). Claims 2-5 and 7 are rejected under 35 U.S.C. § 103(a). Applicants respectfully traverse these rejections for at least the reasons stated below and respectfully request that the Examiner reconsider and withdraw all outstanding rejections.

Attached hereto is a marked-up version of the changes made to the specification by the current amendment. The attached page is captioned "Version with markings to show changes made."